



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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企业微信二维码



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## Features

- $BV_{CEO} > 60V$
- $I_C = 1A$  high Continuous Collector Current
- $I_{CM} = 2A$  Peak Pulse Current
- High Gain device  $> 500$  at  $I_C = 150mA$

## Mechanical Data

- Case: SOT89
- Case Material: Molded Plastic. "Green" Molding Compound. UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 
- Weight: 0.055 grams (Approximate)

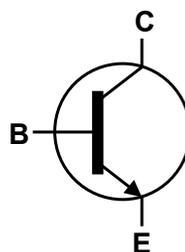
## Applications

- Voltage Regulator Transistors
- Startup Switches
- Darlington Replacement
- DC Fans
- Relays and Solenoid Driving

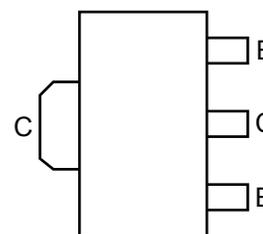
SOT89



Top View



Equivalent Circuit



Top View  
Pin-Out

**Absolute Maximum Ratings** (@ $T_A = +25^{\circ}\text{C}$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	120	V
Collector-Emitter Voltage	$V_{CEO}$	60	V
Emitter-Base Voltage	$V_{EBO}$	7	V
Continuous Collector Current	$I_C$	1	A
Peak Pulse Current	$I_{CM}$	2	A

**Thermal Characteristics** (@ $T_A = +25^{\circ}\text{C}$ , unless otherwise specified.)

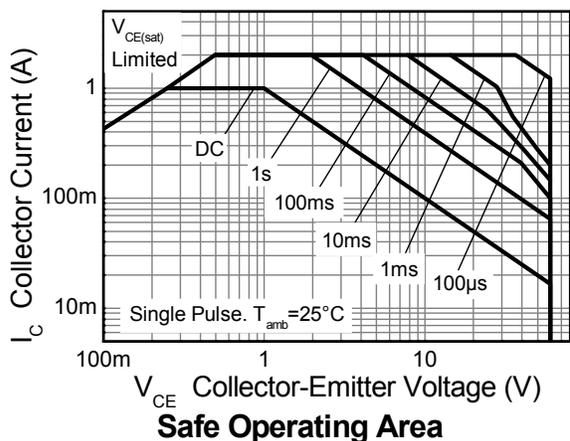
Characteristic	Symbol	Value	Unit
Power Dissipation	$P_D$	(Note 4)	1
		(Note 5)	1.5
		(Note 6)	2.0
Thermal Resistance, Junction to Ambient Air	$R_{\theta JA}$	(Note 4)	125
		(Note 5)	83
		(Note 6)	60
Thermal Resistance, Junction to Lead	$R_{\theta JL}$	22	$^{\circ}\text{C/W}$
Thermal Resistance, Junction to Case	$R_{\theta JC}$	16	
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to +150	$^{\circ}\text{C}$

**ESD Ratings** (Note 9)

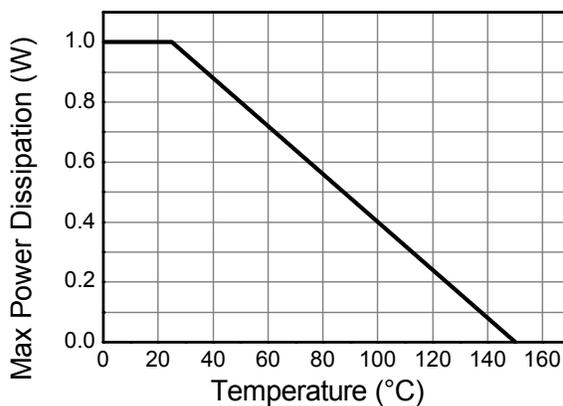
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
4. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
  5. Same as note (4), except the device is mounted on 25mm x 25mm 1oz copper.
  6. Same as note (4), except the device is mounted on 50mm x 50mm 1oz copper.
  7. Thermal resistance from junction to solder-point (on the exposed collector pad).
  8. Thermal resistance from junction to the top of the case.
  9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

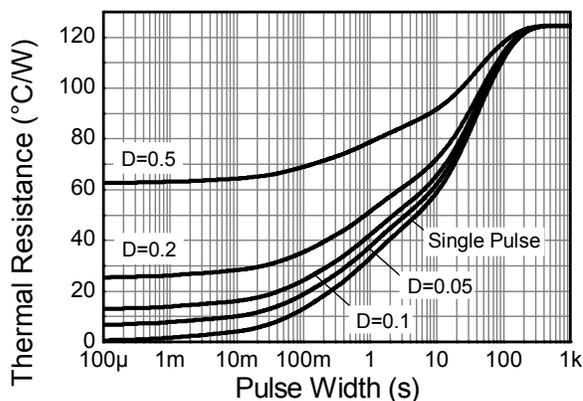
**Thermal Characteristics and Derating Information**



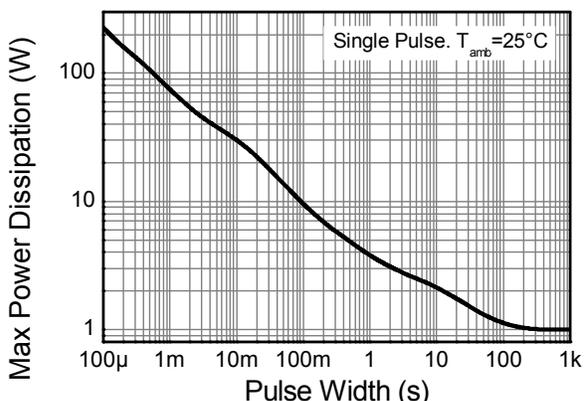
**Safe Operating Area**



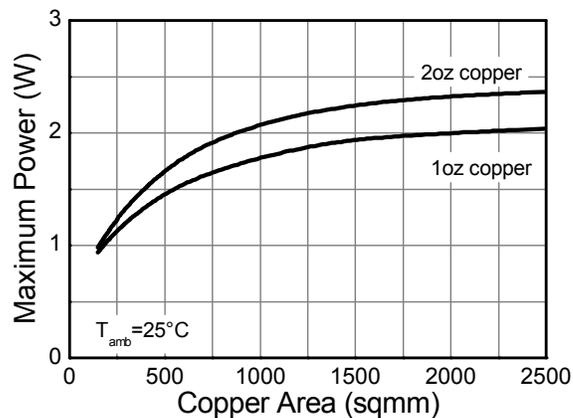
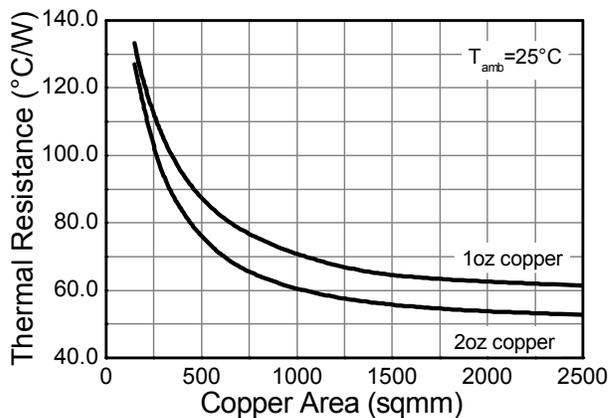
**Derating Curve**



**Transient Thermal Impedance**



**Pulse Power Dissipation**

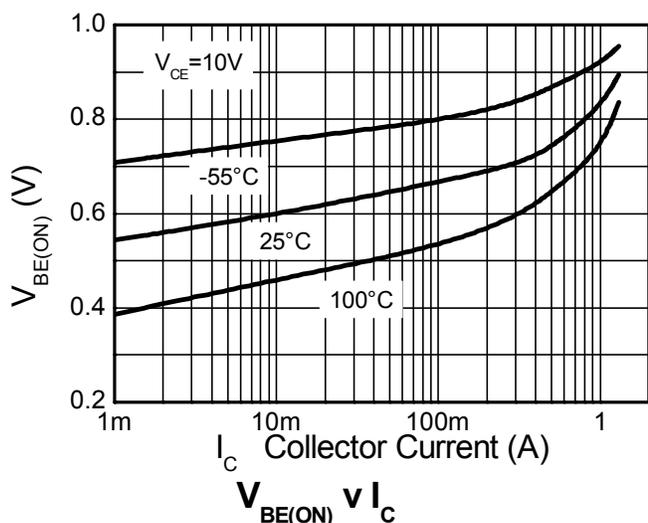
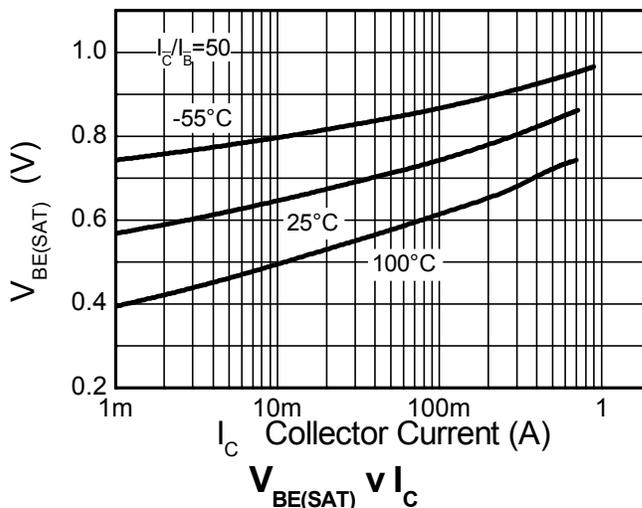
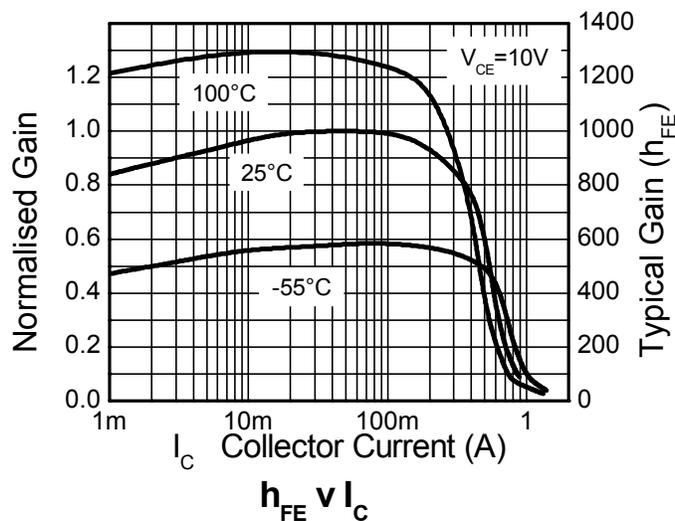
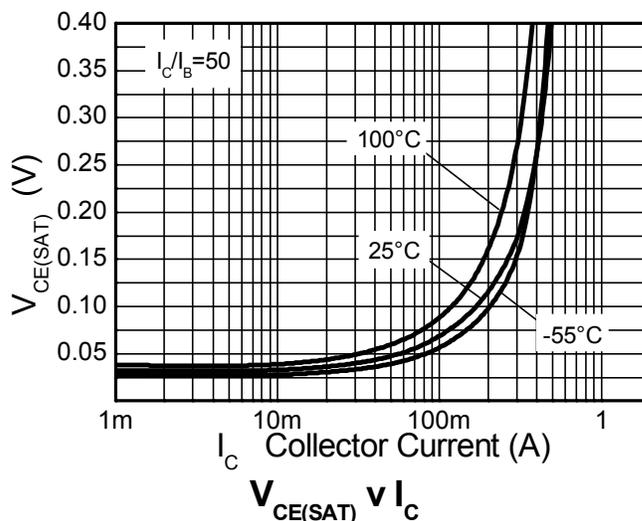
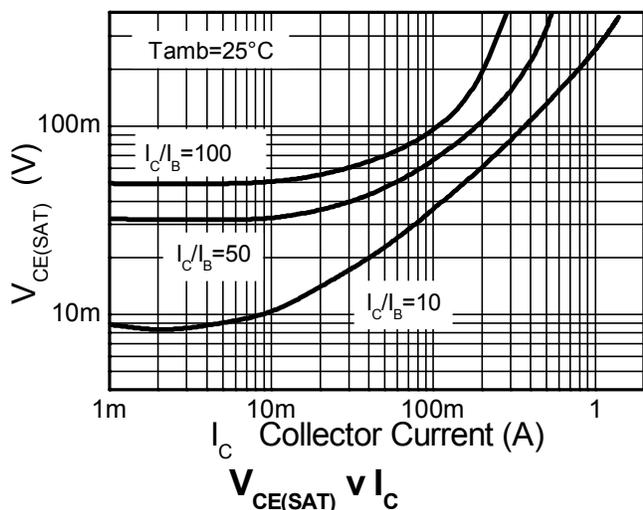


**Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

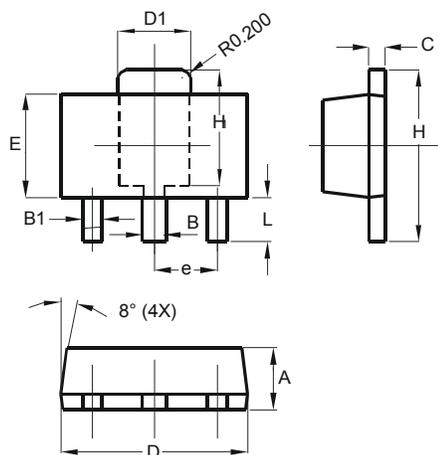
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$BV_{CBO}$	120			V	$I_C = 100 \mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 10)	$BV_{CEO}$	60			V	$I_C = 10\text{mA}$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	7			V	$I_E = 100 \mu\text{A}$
Collector-Base Cutoff Current	$I_{CBO}$			100	nA	$V_{CB} = 45\text{V}$
Collector Cutoff Current	$I_{CES}$			100	nA	$V_{CES} = 45\text{V}$
Emitter Cutoff Current	$I_{EBO}$			100	nA	$V_{EB} = 5\text{V}$
Collector-Emitter Saturation Voltage (Note 10)	$V_{CE(sat)}$			250 500	mV	$I_C = 500\text{mA}, I_B = 50\text{mA}$ $I_C = 1\text{A}, I_B = 100\text{mA}$
Base-Emitter Saturation Voltage (Note 10)	$V_{BE(sat)}$			1.15	V	$I_C = 1\text{A}, I_B = 100\text{mA}$
Base-Emitter Turn-On Voltage (Note 10)	$V_{BE(on)}$			1.0	V	$I_C = 1\text{A}, V_{CE} = 10\text{V}$
DC Current Gain (Note 10)	$h_{FE}$	300 500 300 100 20		1200		$I_C = 1\text{mA}, V_{CE} = 10\text{V}$ $I_C = 150\text{mA}, V_{CE} = 10\text{V}$ $I_C = 250\text{mA}, V_{CE} = 10\text{V}$ $I_C = 500\text{mA}, V_{CE} = 10\text{V}$ $I_C = 1\text{A}, V_{CE} = 10\text{V}$
Transitional Frequency	$f_T$	150			MHz	$I_C = 50\text{mA}, V_{CE} = 10\text{V}$ $f = 100\text{MHz}$
Output capacitance	$C_{obo}$		10		pF	$V_{CB} = 10\text{V}, f = 1\text{MHz}$

 Notes: 10. Measured under pulsed conditions. Pulse width  $\leq 300\mu\text{s}$ . Duty cycle  $\leq 2\%$

**Typical Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

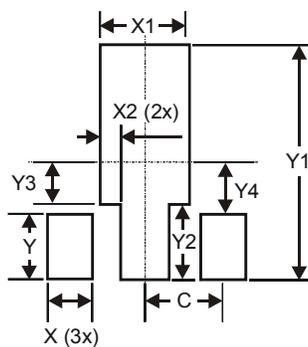


### Package Outline Dimensions



SOT89		
Dim	Min	Max
A	1.40	1.60
B	0.44	0.62
B1	0.35	0.54
C	0.35	0.44
D	4.40	4.60
D1	1.62	1.83
E	2.29	2.60
e	1.50 Typ	
H	3.94	4.25
H1	2.63	2.93
L	0.89	1.20
All Dimensions in mm		

### Suggested Pad Layout



Dimensions	Value (in mm)
X	0.900
X1	1.733
X2	0.416
Y	1.300
Y1	4.600
Y2	1.475
Y3	0.950
Y4	1.125
C	1.500